

### 2SB1260 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.5 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -1 A

Collector-base voltage

$V_{(BR)CBO}$ : -80 V

Operating and storage junction temperature range

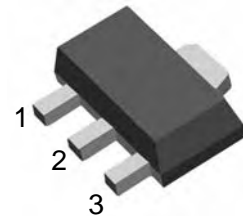
$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-80		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60V, I_E=0$		-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V, I_C=0$		-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-3V, I_C=-0.1A$	82	390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.4	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-50mA$ $f = 30MHz$	80		MHz

#### CLASSIFICATION OF $h_{FE}$

Rank	P	Q	R
Range	82-180	120-270	180-390

Marking	ZL
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